

Abstract

Method for the production of a vertical MOS transistor.

In order to produce a vertical MOS transistor, a mask (13) with an opening is formed on a semiconductor substrate. A layer sequence (14), which has a lower source/drain region (141), a channel region (142) and an upper source/drain region (143), is grown in the opening by selective epitaxy. In this case, facets are formed on the edge, so that the layer thicknesses at the edge are less than in the middle. A gate dielectric (16) and a gate electrode are formed on the edge of the layer sequence.

Figure 3

G E N E R A T E D B Y S I G N A L